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SEMICONDUCTOR



ESD



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PLED

MSK30N03DF

Product specification

Description

The MSK30N03DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

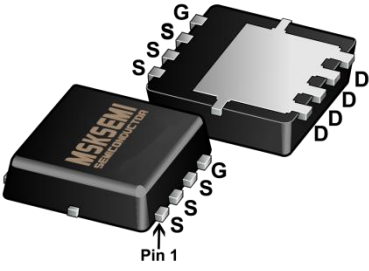
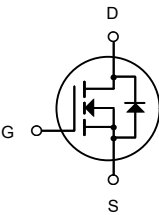
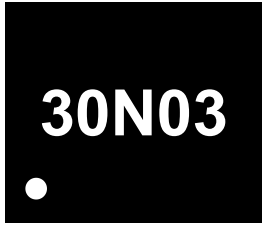
General Features

- $V_{DS} = 30V$ $I_D = 30 A$
- $R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 <p>DFN3X3-8L</p>		

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	30	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	18	A
IDM	Pulsed Drain Current ²	55	A
EAS	Single Pulse Avalanche Energy ³	22.1	mJ
IAS	Avalanche Current	21	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	20	W
TSTG	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance Junction-ambient ¹	75	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	6	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.022	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =10A	---	9	13	mΩ
		V _{GS} =4.5V , I _D =5A	---	12	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.1	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V , V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =1A	---	4.5	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V , V _{GS} =4.5V , I _D =10A	---	7.2	---	nC
Q _{gs}	Gate-Source Charge		---	1.4	---	
Q _{gd}	Gate-Drain Charge		---	2.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =12V , V _{GS} =10V , R _G =3.3 I _D =5A	---	4.1	---	ns
T _r	Rise Time		---	9.8	---	
T _{d(off)}	Turn-Off Delay Time		---	15.5	---	
T _f	Fall Time		---	6.0	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	572	---	pF
C _{oss}	Output Capacitance		---	81	---	
C _{rss}	Reverse Transfer Capacitance		---	65	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	28	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	55	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=21A
- 4 .The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{BM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

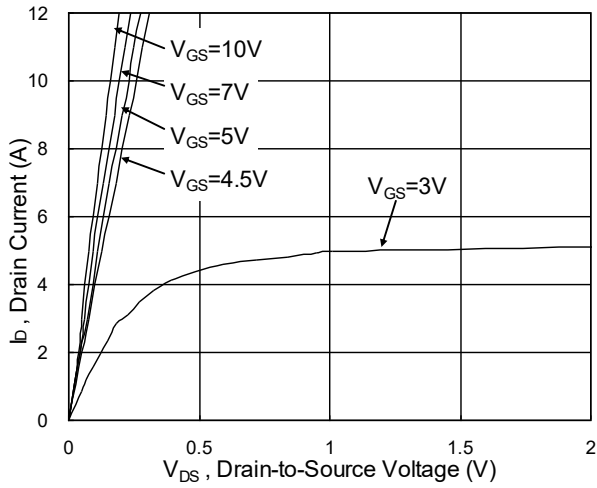


Fig.1 Typical Output Characteristics

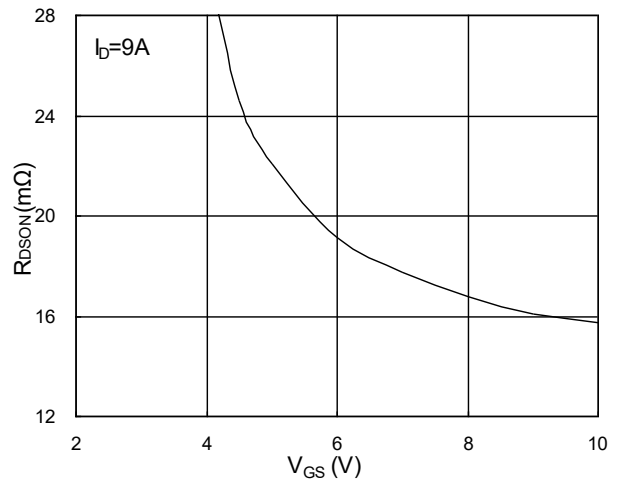


Fig.2 On-Resistance vs. Gate-Source

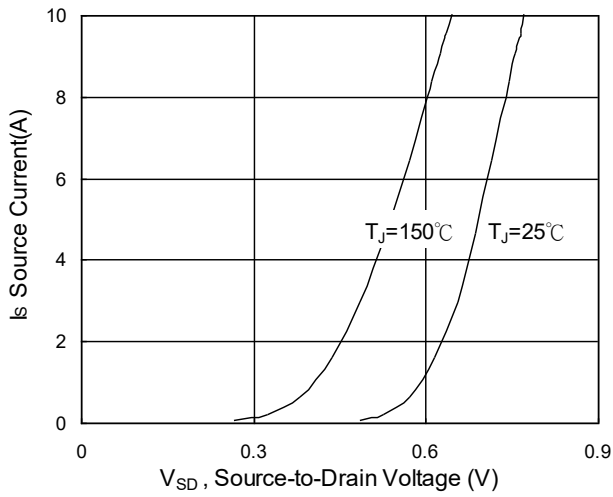


Fig.3 Forward Characteristics Of Reverse

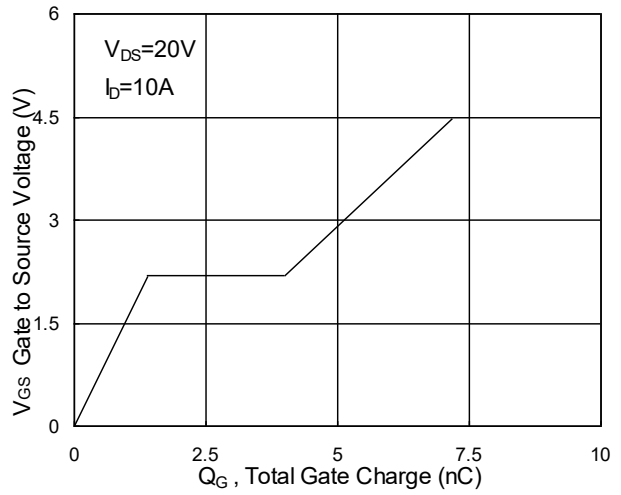


Fig.4 Gate-Charge Characteristics

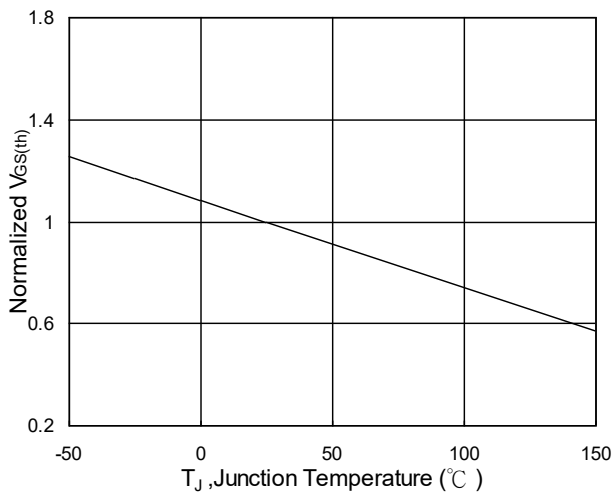


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

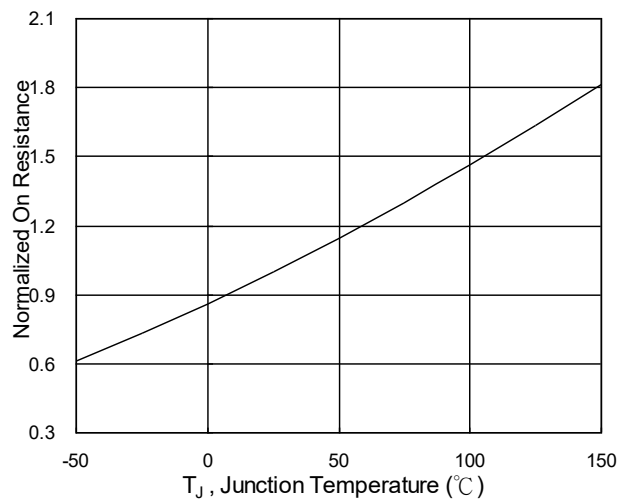


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

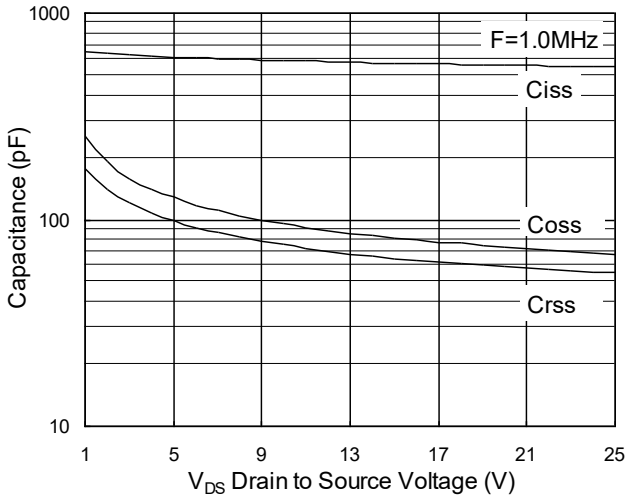


Fig.7 Capacitance

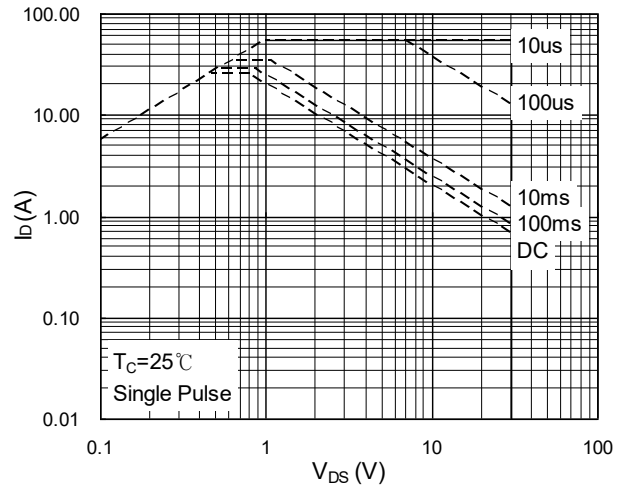


Fig.8 Safe Operating Area

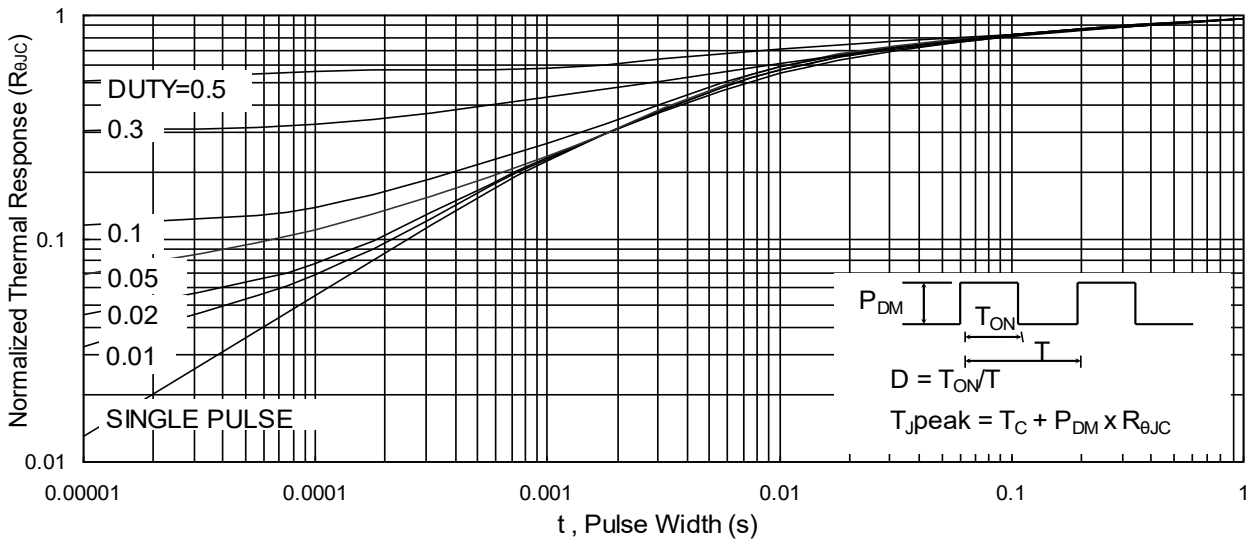


Fig.9 Normalized Maximum Transient Thermal Impedance

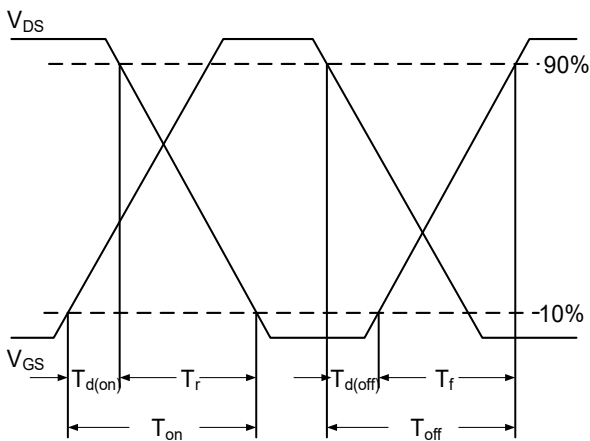


Fig.10 Switching Time Waveform

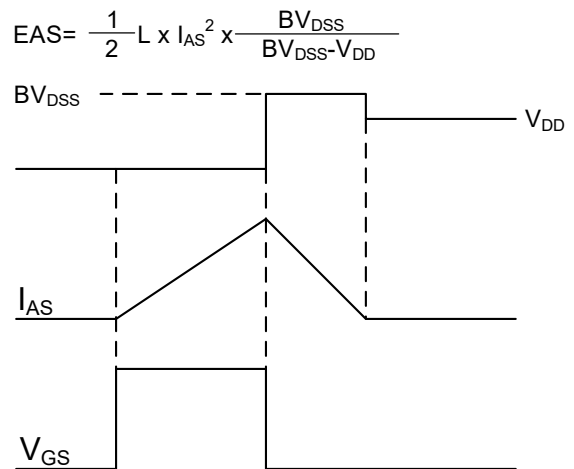
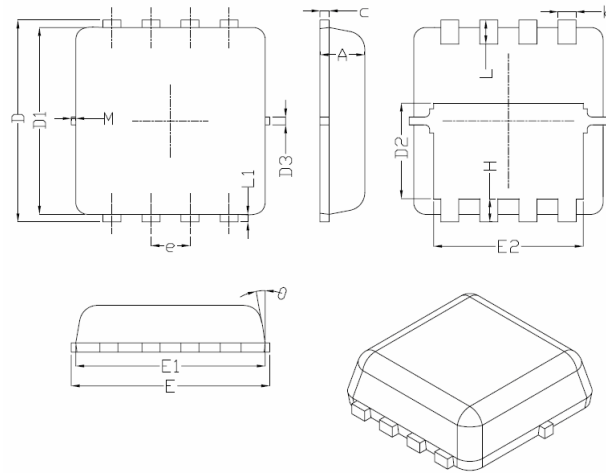


Fig.11 Unclamped Inductive Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REELSPECIFICATION

P/N	PKG	QTY
MSK30N03DF	DFN3X3-8L	5000

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